

In the Claims:

1. (Currently Amended) A method for manufacturing MTJ cell of MRAM comprising:
 - forming a metal layer for a connection ~~connection~~-layer connected to a semiconductor substrate through a lower insulating layer;
 - forming a pinned magnetic layer on the metal layer;
 - physically impacting a surface of the pinned magnetic layer with an atom to form an amorphous layer thereon;
 - sequentially forming a tunneling barrier layer, a free magnetic layer and a MTJ capping layer on the amorphous layer; and
 - patterning the MTJ capping layer, the free magnetic layer, the tunneling barrier layer, amorphous layer and the pinned magnetic layer using a MTJ cell mask to form a MTJ cell.
2. (Currently Amended) The method according to claim 1, wherein the atom is selected from ~~form~~ the group consisting of P or As.